

No.1885C

## LFB01,01L

Silicon Planar Leadless Type

Very High-Speed Switching Diode

#### **Features**

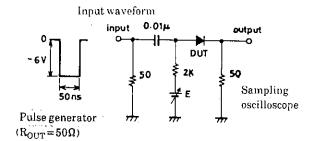
- · Highly reliable leadless glass sleeve structure.
- · Very small size.
- · Capable of being surface-mounted.
- · Forward voltage:  $V_F \max = 1.2V$ .
- · Interterminal capacitance: c max = 3pF.
- · Reverse recovery time:  $t_{rr} max = 4ns$ .

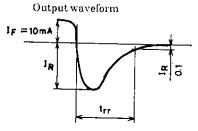
| Absolute Maximum Ratings a  | t Ta = 25°C      | LFB01L        | LFB01         | unit |
|-----------------------------|------------------|---------------|---------------|------|
| Peak Reverse Voltage        | $V_{RM}$         | - 55          | -90           | V    |
| Reverse Voltage             | $V_R$            | -50           | -80           | v    |
|                             | I <sub>FM</sub>  | $\rightarrow$ | 480           | mÅ   |
| Average Rectified Current   | $I_{\mathbf{O}}$ | <b>→</b>      | 150           | mA   |
| Surge Current               | I <sub>FSM</sub> | $\rightarrow$ | 2             | A    |
| Allowable Power Dissipation | P                | $\rightarrow$ | 300           | mW   |
|                             | Tj               | $\rightarrow$ | +175          | °C   |
| Storage Temperature         | Tstg             | <b>→</b>      | -65  to  +175 | °Č   |

#### Electrical Characteristics at Ta = 25°C

| recorded that accessing | 5 at 1 a — Zi                |   | min | tvp | max  | unit |
|-------------------------|------------------------------|---|-----|-----|------|------|
| Forward Voltage         | $ m V_{F}$                   | $I_F = 100 \text{mA}$                                 |     | . J | 1.2  | V    |
| Reverse Current         | $I_{R}1$                     | $V_R = -30V$  |     |     | -0.1 | иÅ   |
|                         | $I_{ m R}2$                  | At each V <sub>R</sub>                                |     |     | -0.5 | иA   |
| Interminal Capacitance  |                              | $V_R = 0V, f = 1MHz$                                  |     |     | 3    | рF   |
| Reverse Recovery Time   | $\mathfrak{t}_{\mathrm{rr}}$ | $V_{R} = -6V, I_{F} = 10 \text{mA}, R_{L} = 50\Omega$ |     |     | 4    | ns   |

### Reverse Recovery Time $(t_{rr})$ Test Circuit





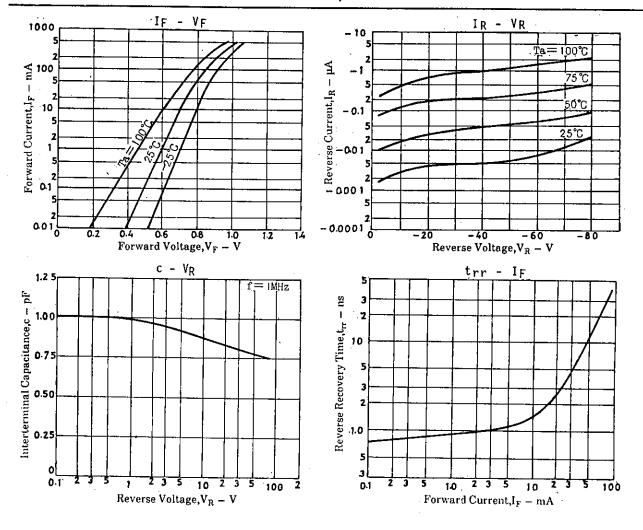
Unit (resistance:  $\Omega$ , capacitance: F)

# Package Dimensions 1137 (unit: mm)

cathode mark



C: Cathode A: Anode



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